		U	
	Application No.	Applicant(s)	
Notice of Allowability	10/695,478	IDOTA ET AL.	
	Examiner	Art Unit	
	Anh D. Mai	2814	
The MAILING DATE of this communication appeal All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communication IGHTS. This application is subject to	plication. If not included will be mailed in due course. TH	IS iative
1. \boxtimes This communication is responsive to <u>the Response filed M</u>	larch 1, 2005.		
2. The allowed claim(s) is/are 1-6,8 and 9.			
3. \boxtimes The drawings filed on <u>29 October 2003</u> are accepted by th	e Examiner.		
 4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: Certified copies of the priority documents have Certified copies of the priority documents have Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	e been received. e been received in Application No		e
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirements	
5. A SUBSTITUTE OATH OR DECLARATION must be subminformal PATENT APPLICATION (PTO-152) which give			
6. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner' Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the sheet is sheet in the sheet in the sheet in the sheet in the sheet is sheet in the	son's Patent Drawing Review (PTO s Amendment / Comment or in the C .84(c)) should be written on the drawin	office action of	
7. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT			
Attachment(s)	E Matta - Elufama - I D	atont Application (DTC 450)	
 Notice of References Cited (PTO-892) Dotice of Draftperson's Patent Drawing Review (PTO-948) 		atent Application (PTO-152)	
	Paper No./Mail Dat	e	
 Information Disclosure Statements (PTO-1449 or PTO/SB/C Paper No./Mail Date 10/29/03 	08), 7. ⊠ Examiner's Amendr	nent/Comment	
4. Examiner's Comment Regarding Requirement for Deposit		ent of Reasons for Allowance	
of Biological Material	9.		

Application/Control Number: 10/695,478 Page 2

Art Unit: 2814

Election/Restrictions

1. Applicant's election without traverse of Group I, claims 1-6, 8 and 9 in the reply filed on March 1, 2005 is acknowledged.

2. This application is in condition for allowance except for the presence of claims 7, 10 and 11 to invention non-elected without traverse. Accordingly, claims 7, 10 and 11 have been cancelled.

EXAMINER'S AMENDMENT

3. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

In the Specifications:

New Title:

METHOD OF FABRICATING A BIPOLAR TRANSISTOR UTILIZING A DRY ETCHING AND A WET ETCHING TO DEFINE A BASE JUNCTION OPENING

In the Claims:

Cancel claims 7, 10 and 11.

Allowable Subject Matter

4. Claims 1-6, 8 and 9 are allowed.

Application/Control Number: 10/695,478

Art Unit: 2814

Page 3

5. The following is an examiner's statement of reasons for allowance: prior art of record fails to teach a method for fabricating a semiconductor device in the combination of limitations as claimed including: a step (d) of forming, on the semiconductor substrate, an etching stopper layer which serves as an etching stopper against dry etching and which has insulating ability and a masking layer against wet etching in such a way that the masking layer overlies the etching stopper layer; a step (e) of exposing a part of the etching stopper layer by removing a part of the masking layer by means of dry etching; a step (f) of forming a base junction opening portion reaching the semiconductor layer by subjecting the part of the etching stopper layer exposed by means of dry etching of step (e) to a wet etching treatment using the remaining part of the masking layer as a mask.

The prior art, in the formation of the base junction opening, teaches: forming a single etch mask layer on the semiconductor layer and performing a dry etch to form the opening.

- 6. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."
- 7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Anh D. Mai whose telephone number is (571) 272-1710. The examiner can normally be reached on 9:00AM-5:00PM.

Application/Control Number: 10/695,478

Art Unit: 2814

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

Page 4

supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

March 15, 2005